



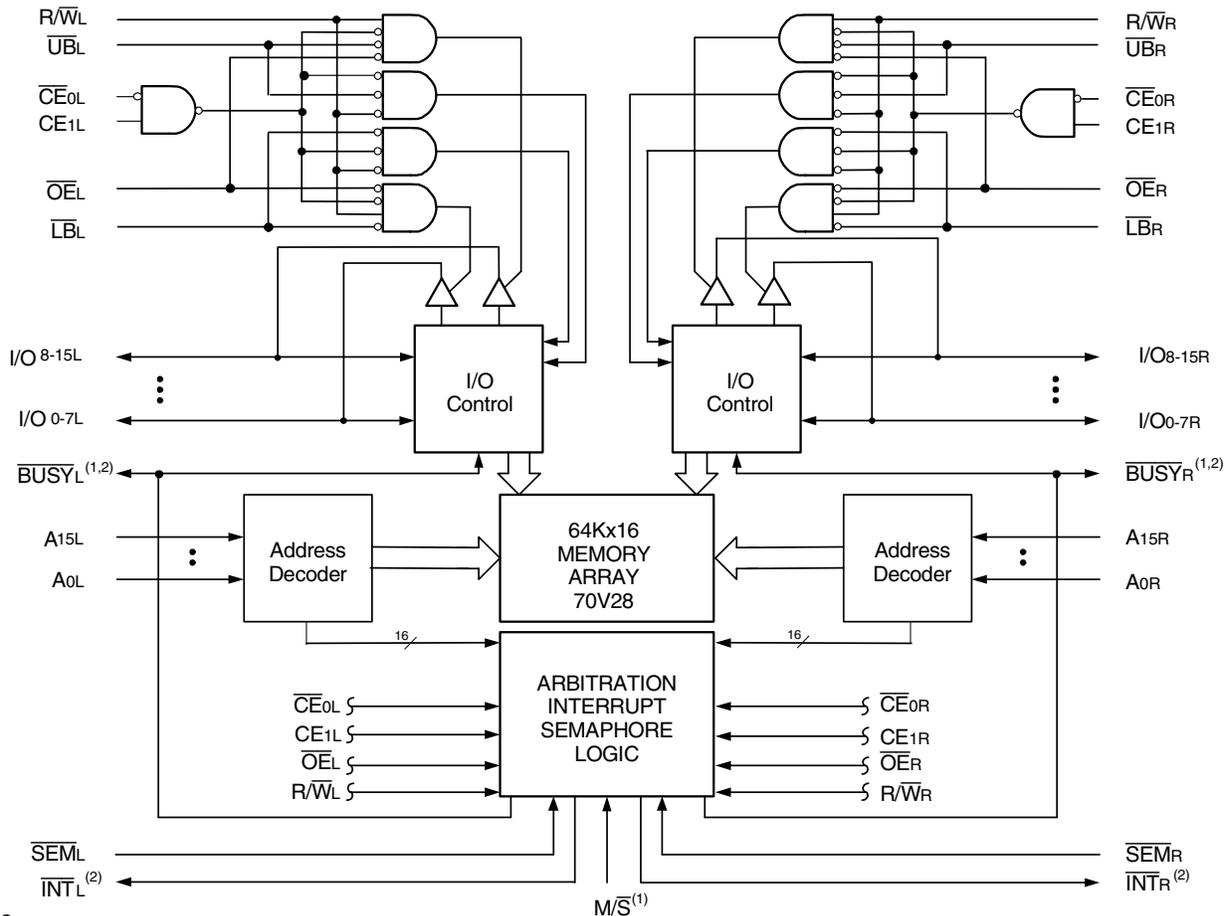
HIGH-SPEED 3.3V 64K x 16 DUAL-PORT STATIC RAM

70V28L

Features

- ◆ True Dual-Ported memory cells which allow simultaneous access of the same memory location
- ◆ High-speed access
 - Commercial: 15/20ns (max.)
 - Industrial: 20ns (max.)
- ◆ Low-power operation
 - IDT70V28L
 - Active: 440mW (typ.)
 - Standby: 660µW (typ.)
- ◆ Dual chip enables allow for depth expansion without external logic
- ◆ IDT70V28 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading more than one device
- ◆ $\overline{M/\overline{S}} = V_{IH}$ for \overline{BUSY} output flag on Master, $\overline{M/\overline{S}} = V_{IL}$ for \overline{BUSY} input on Slave
- ◆ Busy and Interrupt Flags
- ◆ On-chip port arbitration logic
- ◆ Full on-chip hardware support of semaphore signaling between ports
- ◆ Fully asynchronous operation from either port
- ◆ Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- ◆ LVTTTL-compatible, single 3.3V ($\pm 0.3V$) power supply
- ◆ Available in a 100-pin TQFP
- ◆ Industrial temperature range ($-40^{\circ}C$ to $+85^{\circ}C$) is available for selected speeds
- ◆ Green parts available, see ordering information

Functional Block Diagram



NOTES:

1. \overline{BUSY} is an input as a Slave ($\overline{M/\overline{S}}=V_{IL}$) and an output when it is a Master ($\overline{M/\overline{S}}=V_{IH}$).
2. \overline{BUSY} and \overline{INT} are non-tri-state totem-pole outputs (push-pull).

4849 drw 01

JUNE 2019

Description

The IDT70V28 is a high-speed 64K x 16 Dual-Port Static RAM. The IDT70V28 is designed to be used as a stand-alone 1024K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit-or-more word system. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

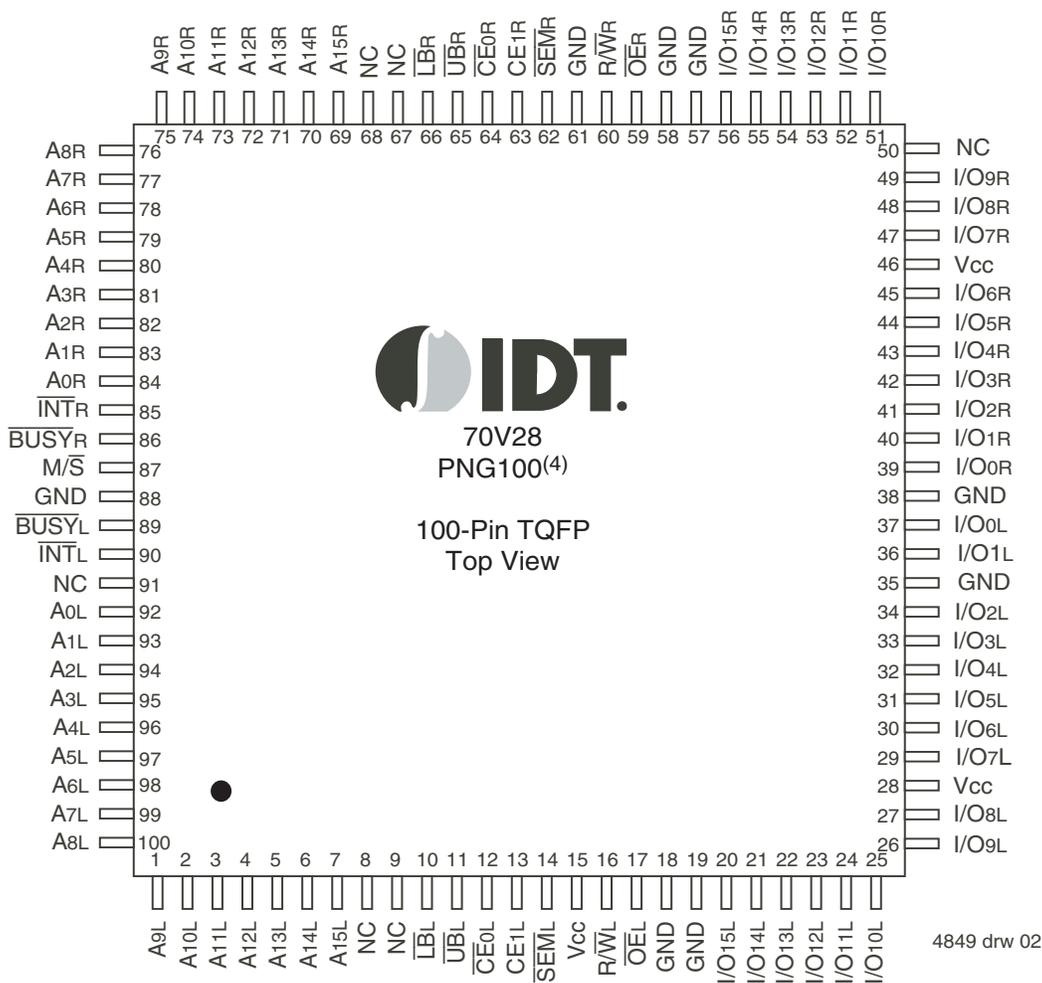
This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access

for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (either $\overline{CE0}$ or $\overline{CE1}$) permit the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 440mW of power.

The IDT70V28 is packaged in a 100-pin Thin Quad Flatpack (TQFP).

Pin Configurations^(1,2,3)



NOTES:

1. All Vcc pins must be connected to power supply.
2. All GND pins must be connected to ground.
3. Package body is approximately 14mm x 14mm x 1.4mm.
4. This package code is used to reference the package diagram.

Pin Names

Left Port	Right Port	Names
\overline{CE}_{0L} , CE1L	\overline{CE}_{0R} , CE1R	Chip Enables
R/ \overline{WL}	R/ \overline{WR}	Read/Write Enable
\overline{OE}_L	\overline{OE}_R	Output Enable
A0L - A15L	A0R - A15R	Address
I/O0L - I/O15L	I/O0R - I/O15R	Data Input/Output
\overline{SEM}_L	\overline{SEM}_R	Semaphore Enable
\overline{UB}_L	\overline{UB}_R	Upper Byte Select
\overline{LB}_L	\overline{LB}_R	Lower Byte Select
\overline{INT}_L	\overline{INT}_R	Interrupt Flag
\overline{BUSY}_L	\overline{BUSY}_R	Busy Flag
M/ \overline{S}		Master or Slave Select
Vcc		Power
GND		Ground

4849 tbl 01

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	50	mA

4849 tbl 02

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{TERM} must not exceed V_{CC} + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of V_{TERM} ≥ V_{CC} + 0.3V.

Maximum Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽¹⁾	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V ± 0.3V
Industrial	-40°C to +85°C	0V	3.3V ± 0.3V

4849 tbl 03

NOTE:

- This is the parameter T_A. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.0	—	V _{CC} +0.3 ⁽²⁾	V
V _{IL}	Input Low Voltage	-0.3 ⁽¹⁾	—	0.8	V

4849 tbl 04

NOTES:

- V_{IL} ≥ -1.5V for pulse width less than 10ns.
- V_{TERM} must not exceed V_{CC} + 0.3V.

Capacitance⁽¹⁾ (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	9	pF
C _{OUT}	Output Capacitance	V _{OUT} = 3dV	10	pF

4849 tbl 05

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Truth Table I – Chip Enable^(1,2)

\overline{CE}	\overline{CE}_0	CE_1	Mode
L	V_{IL}	V_{IH}	Port Selected (TTL Active)
	$\leq 0.2V$	$\geq V_{CC} - 0.2V$	Port Selected (CMOS Active)
H	V_{IH}	X	Port Deselected (TTL Inactive)
	X	V_{IL}	Port Deselected (TTL Inactive)
	$\geq V_{CC} - 0.2V$	$X^{(3)}$	Port Deselected (CMOS Inactive)
	$X^{(3)}$	$\leq 0.2V$	Port Deselected (CMOS Inactive)

4849tbl 06

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE_1 levels; \overline{CE} is a reference only.
2. 'H' = V_{IH} and 'L' = V_{IL} .
3. CMOS standby requires 'X' to be either $\leq 0.2V$ or $\geq V_{CC} - 0.2V$.

Truth Table II – Non-Contention Read/Write Control

Inputs ⁽¹⁾						Outputs		Mode
$\overline{CE}^{(2)}$	R/ \overline{W}	\overline{OE}	\overline{UB}	\overline{LB}	\overline{SEM}	I/O ₈₋₁₅	I/O ₀₋₇	
H	X	X	X	X	H	High-Z	High-Z	Deselected: Power-Down
X	X	X	H	H	H	High-Z	High-Z	Both Bytes Deselected
L	L	X	L	H	H	DATA _{IN}	High-Z	Write to Upper Byte Only
L	L	X	H	L	H	High-Z	DATA _{IN}	Write to Lower Byte Only
L	L	X	L	L	H	DATA _{IN}	DATA _{IN}	Write to Both Bytes
L	H	L	L	H	H	DATA _{OUT}	High-Z	Read Upper Byte Only
L	H	L	H	L	H	High-Z	DATA _{OUT}	Read Lower Byte Only
L	H	L	L	L	H	DATA _{OUT}	DATA _{OUT}	Read Both Bytes
X	X	H	X	X	X	High-Z	High-Z	Outputs Disabled

4849 tbl 07

NOTES:

1. A_{0L} – A_{15L} ≠ A_{0R} – A_{15R}
2. Refer to Truth Table I - Chip Enable.

Truth Table III – Semaphore Read/Write Control⁽¹⁾

Inputs ⁽¹⁾						Outputs		Mode
$\overline{CE}^{(2)}$	R/ \overline{W}	\overline{OE}	\overline{UB}	\overline{LB}	\overline{SEM}	I/O ₈₋₁₅	I/O ₀₋₇	
H	H	L	X	X	L	DATA _{OUT}	DATA _{OUT}	Read Data in Semaphore Flag
X	H	L	H	H	L	DATA _{OUT}	DATA _{OUT}	Read Data in Semaphore Flag
H	↑	X	X	X	L	DATA _{IN}	DATA _{IN}	Write I/O ₀ into Semaphore Flag
X	↑	X	H	H	L	DATA _{IN}	DATA _{IN}	Write I/O ₀ into Semaphore Flag
L	X	X	L	X	L	—	—	Not Allowed
L	X	X	X	L	L	—	—	Not Allowed

4849 tbl 08

NOTES:

1. There are eight semaphore flags written to I/O₀ and read from all the I/Os (I/O₀-I/O₁₅). These eight semaphore flags are addressed by A₀-A₂.
2. Refer to Truth Table I - Chip Enable.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($V_{CC} = 3.3V \pm 0.3V$)

Symbol	Parameter	Test Conditions	70V28L		Unit
			Min.	Max.	
$ I_{LI} $	Input Leakage Current ⁽¹⁾	$V_{CC} = 3.6V, V_{IN} = 0V \text{ to } V_{CC}$	—	5	μA
$ I_{LO} $	Output Leakage Current	$\overline{CE}^{(2)} = V_{IH}, V_{OUT} = 0V \text{ to } V_{CC}$	—	5	μA
V_{OL}	Output Low Voltage	$I_{OL} = +4mA$	—	0.4	V
V_{OH}	Output High Voltage	$I_{OH} = -4mA$	2.4	—	V

NOTES:

- At $V_{CC} \leq 2.0V$, input leakages are undefined.
- Refer to Truth Table I - Chip Enable.

4849 tbl 09

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾ ($V_{CC} = 3.3V \pm 0.3V$)

Symbol	Parameter	Test Condition	Version	70V28L15 Com'l Only		70V28L20 Com'l & Ind		Unit
				Typ. ⁽¹⁾	Max.	Typ. ⁽¹⁾	Max.	
I_{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = V_{IL}$, Outputs Disabled $SEM = V_{IH}$ $f = f_{MAX}^{(2)}$	COM'L L	145	235	135	205	mA
			IND L	—	—	135	220	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_L = \overline{CE}_R = V_{IH}$ $SEM_R = SEM_L = V_{IH}$ $f = f_{MAX}^{(2)}$	COM'L L	40	70	35	55	mA
			IND L	—	—	35	65	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^*_{A} = V_{IL}$ and $\overline{CE}^*_{B} = V_{IH}^{(4)}$ Active Port Outputs Disabled, $f = f_{MAX}^{(2)}$, $SEM_R = SEM_L = V_{IH}$	COM'L L	100	155	90	140	mA
			IND L	—	—	90	150	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports \overline{CE}_L and $\overline{CE}_R \geq V_{CC} - 0.2V$, $V_{IN} > V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, $f = 0^{(3)}$ $SEM_R = SEM_L \geq V_{CC} - 0.2V$	COM'L L	0.2	3.0	0.2	3.0	mA
			IND L	—	—	0.2	3.0	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}^*_{A} \leq 0.2V$ and $\overline{CE}^*_{B} \geq V_{CC} - 0.2V^{(4)}$, $SEM_R = SEM_L \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, Active Port Outputs Disabled, $f = f_{MAX}^{(2)}$	COM'L L	95	150	90	135	mA
			IND L	—	—	90	145	

NOTES:

- $V_{CC} = 3.3V$, $T_A = +25^\circ C$, and are not production tested. $I_{CCDC} = 90mA$ (Typ.)
- At $f = f_{MAX}$, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.
- $f = 0$ means no address or control lines change.
- Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- Refer to Truth Table I - Chip Enable.

4849 tbl 10

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

4849 tbl 11

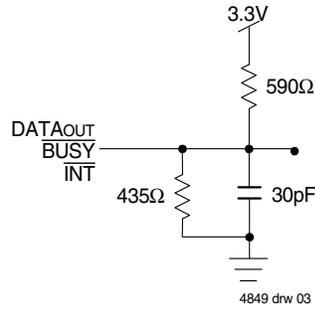


Figure 1. AC Output Load

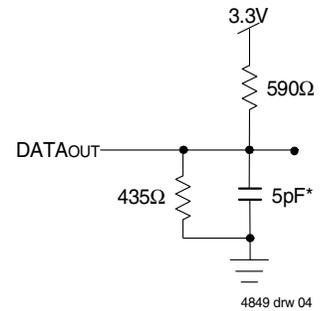
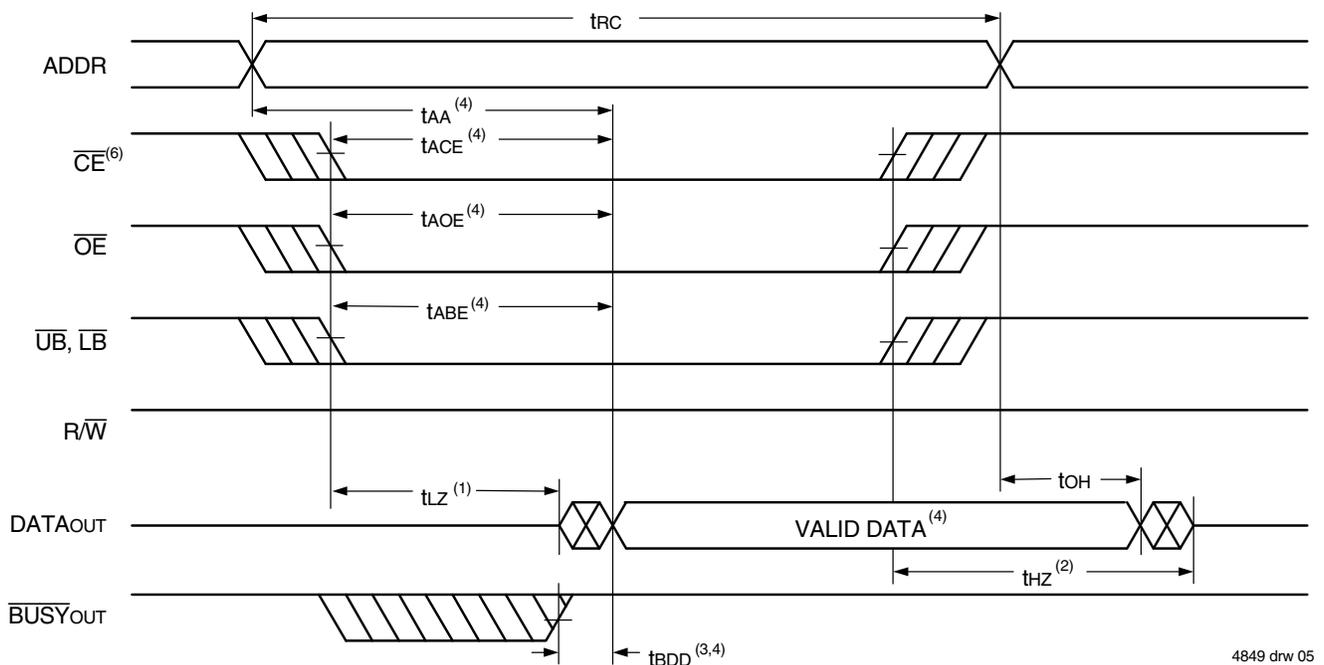


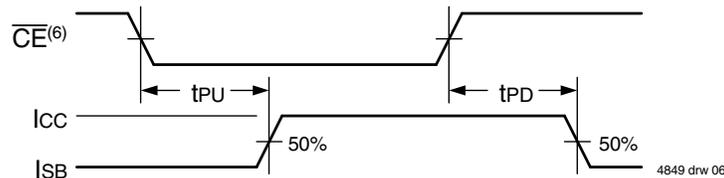
Figure 2. Output Test Load
(for tLZ, tHZ, twz, tow)
* Including scope and jig.

Waveform of Read Cycles⁽⁵⁾



4849 drw 05

Timing of Power-Up Power-Down



4849 drw 06

NOTES:

- Timing depends on which signal is asserted last, \overline{OE} , \overline{CE} , \overline{LB} or \overline{UB} .
- Timing depends on which signal is de-asserted first, \overline{CE} , \overline{OE} , \overline{LB} or \overline{UB} .
- t_{BDD} delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations \overline{BUSY} has no relation to valid output data.
- Start of valid data depends on which timing becomes effective last t_{AOE} , t_{ACE} , t_{AA} or t_{BDD} .
- $\overline{SEM} = V_{IH}$.
- Refer to Truth Table I - Chip Enable

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

Symbol	Parameter	70V28L15 Com'l Only		70V28L20 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t _{RC}	Read Cycle Time	15	—	20	—	ns
t _{AA}	Address Access Time	—	15	—	20	ns
t _{ACE}	Chip Enable Access Time ⁽³⁾	—	15	—	20	ns
t _{ABE}	Byte Enable Access Time ⁽³⁾	—	15	—	20	ns
t _{AOE}	Output Enable Access Time	—	10	—	12	ns
t _{OH}	Output Hold from Address Change	3	—	3	—	ns
t _{LZ}	Output Low-Z Time ^(1,2)	3	—	3	—	ns
t _{HZ}	Output High-Z Time ^(1,2)	—	10	—	10	ns
t _{PU}	Chip Enable to Power Up Time ⁽²⁾	0	—	0	—	ns
t _{PD}	Chip Disable to Power Down Time ⁽²⁾	—	15	—	20	ns
t _{SOP}	Semaphore Flag Update Pulse (\overline{OE} or \overline{SEM})	10	—	10	—	ns
t _{SAA}	Semaphore Address Access Time	—	15	—	20	ns

4849 tbl 12

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage

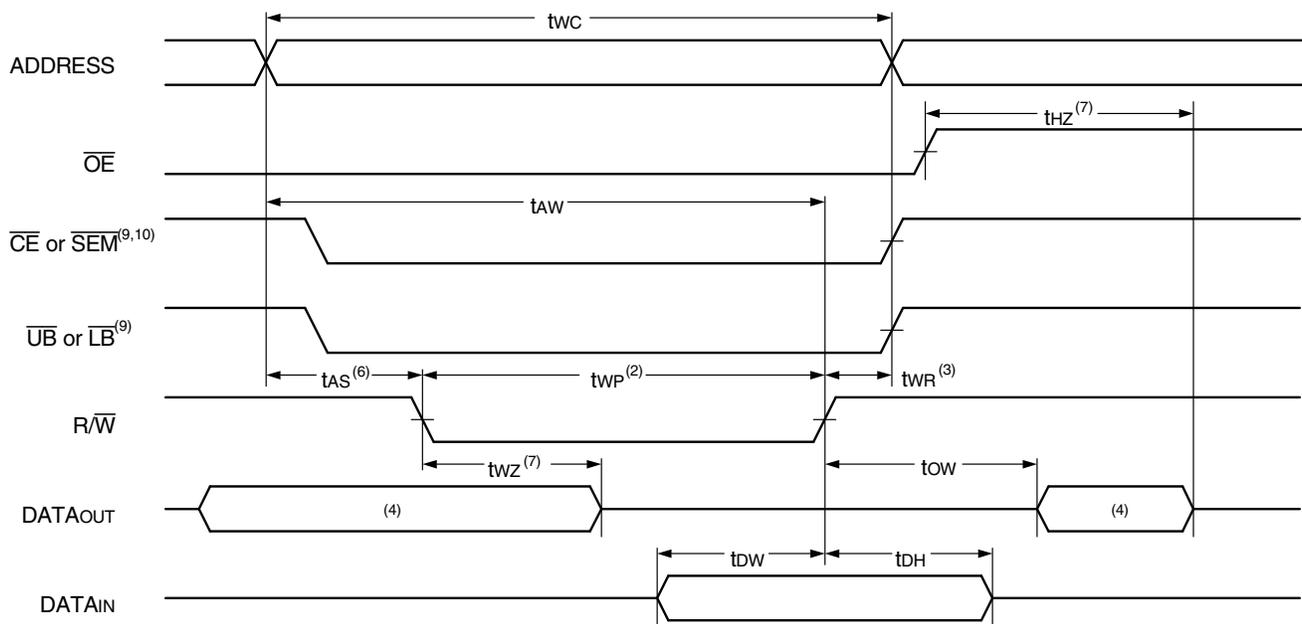
Symbol	Parameter	70V28L15 Com'l Only		70V28L20 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
WRITE CYCLE						
t _{WC}	Write Cycle Time	15	—	20	—	ns
t _{EW}	Chip Enable to End-of-Write ⁽³⁾	12	—	15	—	ns
t _{AW}	Address Valid to End-of-Write	12	—	15	—	ns
t _{AS}	Address Set-up Time ⁽³⁾	0	—	0	—	ns
t _{WP}	Write Pulse Width	12	—	15	—	ns
t _{WR}	Write Recovery Time	0	—	0	—	ns
t _{DW}	Data Valid to End-of-Write	10	—	15	—	ns
t _{HZ}	Output High-Z Time ^(1,2)	—	10	—	10	ns
t _{DH}	Data Hold Time ⁽⁴⁾	0	—	0	—	ns
t _{WZ}	Write Enable to Output in High-Z ^(1,2)	—	10	—	10	ns
t _{OW}	Output Active from End-of-Write ^(1,2,4)	0	—	0	—	ns
t _{SWRD}	\overline{SEM} Flag Write to Read Time	5	—	5	—	ns
t _{SPS}	\overline{SEM} Flag Contention Window	5	—	5	—	ns

4849 tbl 13

NOTES:

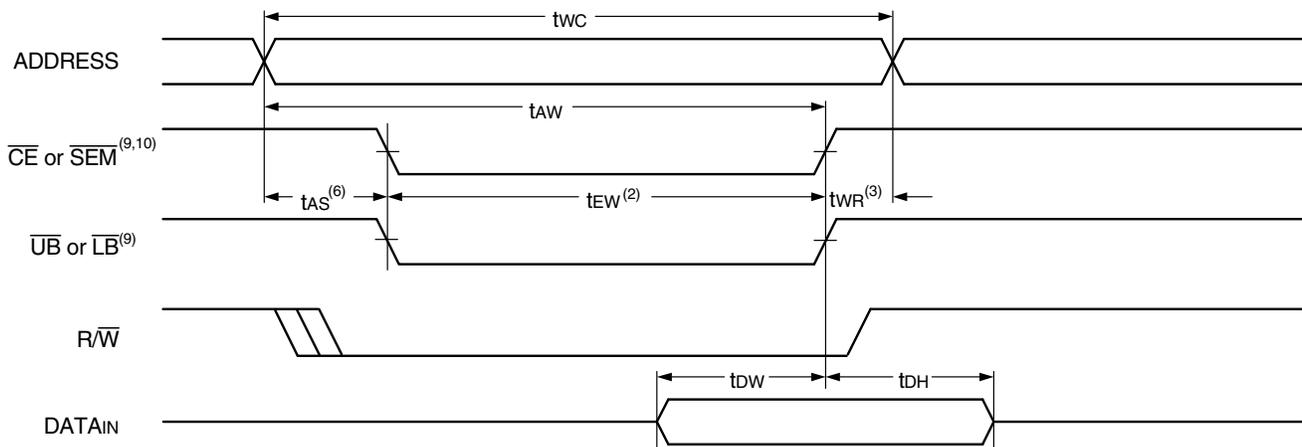
1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
2. This parameter is guaranteed by device characterization, but is not production tested.
3. To access RAM, $\overline{CE} = V_{IL}$ and $\overline{SEM} = V_{IH}$. To access semaphore, $\overline{CE} = V_{IH}$ and $\overline{SEM} = V_{IL}$. Either condition must be valid for the entire t_{EW} time.
4. The specification for t_{DH} must be met by the device supplying write data to the RAM under all operating conditions. Although t_{DH} and t_{OW} values will vary over voltage and temperature, the actual t_{DH} will always be smaller than the actual t_{OW}.

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)



4849 drw 07

Timing Waveform of Write Cycle No. 2, CE Controlled Timing^(1,5)

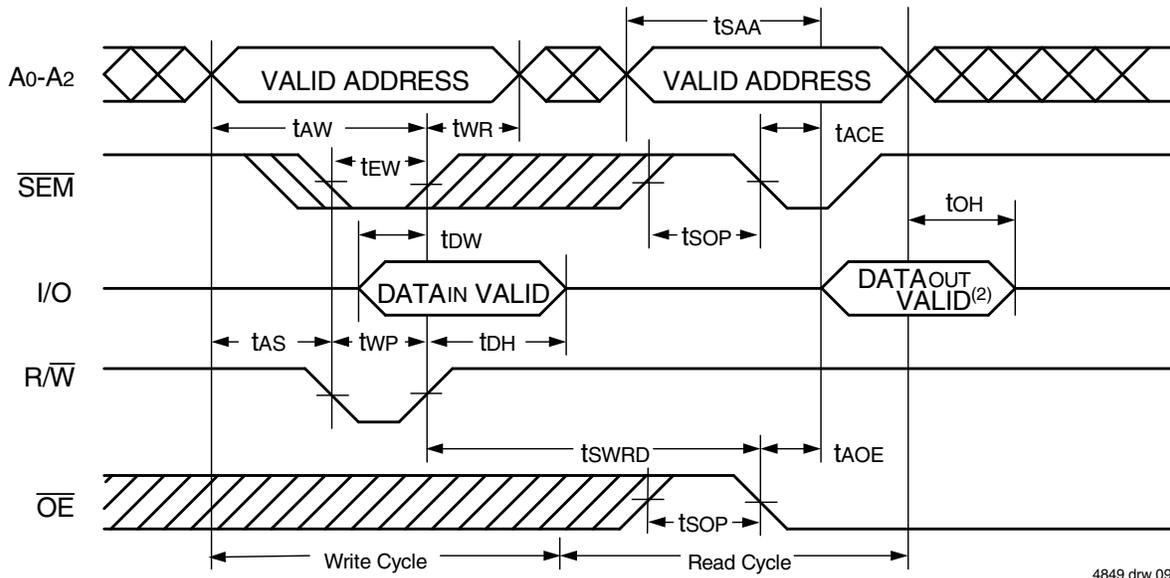


4849 drw 08

NOTES:

1. R/W or CE or UB and LB = VIH during all address transitions.
2. A write occurs during the overlap (tEW or tWP) of a CE = VIL and a R/W = VIL for memory array writing cycle.
3. tWR is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
4. During this period, the I/O pins are in the output state and input signals must not be applied.
5. If the CE or SEM = VIL transition occurs simultaneously with or after the R/W = VIL transition, the outputs remain in the High-impedance state.
6. Timing depends on which enable signal is asserted last, CE or R/W.
7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
8. If OE = VIL during R/W controlled write cycle, the write pulse width must be the larger of tWP or (tWZ + tOW) to allow the I/O drivers to turn off and data to be placed on the bus for the required tOW. If OE = VIH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified tWP.
9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tEW must be met for either condition.
10. Refer to Truth Table I - Chip Enable.

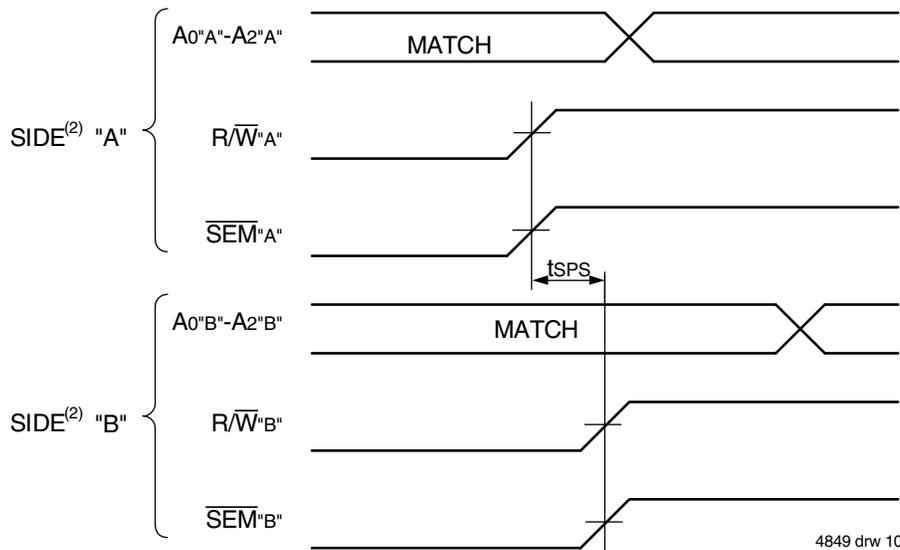
Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

1. $\overline{CE} = V_{IH}$ or \overline{UB} and $\overline{LB} = V_{IH}$ for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table).
2. "DATA OUT VALID" represents all I/O's (I/O₀ - I/O₁₅) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



NOTES:

1. $D_{OR} = D_{OL} = V_{IL}$, $\overline{CE}_L = \overline{CE}_R = V_{IH}$ or both \overline{UB} and $\overline{LB} = V_{IH}$ (Refer to Chip Enable Truth Table).
2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
3. This parameter is measured from R/\overline{W}^A or \overline{SEM}^A going HIGH to R/\overline{W}^B or \overline{SEM}^B going HIGH.
4. If t_{SPS} is not satisfied the semaphore will fall positively to one side or the other, but there is no guarantee which side will be granted the semaphore flag.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

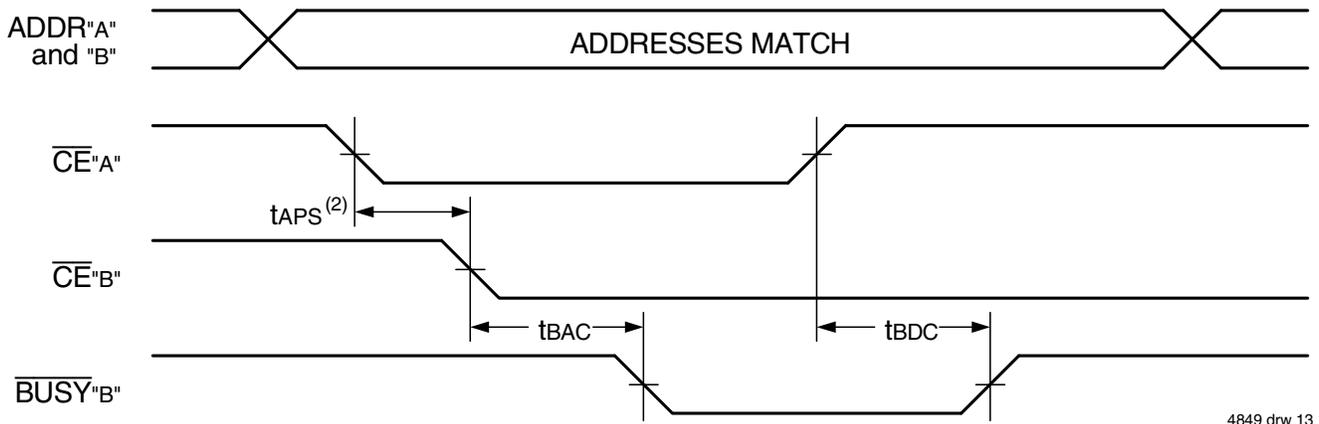
Symbol	Parameter	70V28L15 Com'l Only		70V28L20 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
BUSY TIMING ($M/\overline{S}=V_{IH}$)						
t _{BAA}	\overline{BUSY} Access Time from Address Match	—	15	—	20	ns
t _{BDA}	\overline{BUSY} Disable Time from Address Not Matched	—	15	—	20	ns
t _{BAC}	\overline{BUSY} Access Time from Chip Enable Low	—	15	—	20	ns
t _{BDC}	\overline{BUSY} Access Time from Chip Enable High	—	15	—	17	ns
t _{APS}	Arbitration Priority Set-up Time ⁽²⁾	5	—	5	—	ns
t _{BDD}	\overline{BUSY} Disable to Valid Data ⁽³⁾	—	15	—	17	ns
t _{WH}	Write Hold After \overline{BUSY} ⁽⁵⁾	12	—	15	—	ns
BUSY TIMING ($M/\overline{S}=V_{IL}$)						
t _{WB}	\overline{BUSY} Input to Write ⁽⁴⁾	0	—	0	—	ns
t _{WH}	Write Hold After \overline{BUSY} ⁽⁵⁾	12	—	15	—	ns
PORT-TO-PORT DELAY TIMING						
t _{WDD}	Write Pulse to Data Delay ⁽¹⁾	—	30	—	45	ns
t _{DDD}	Write Data Valid to Read Data Delay ⁽¹⁾	—	25	—	30	ns

4849 tbl 14

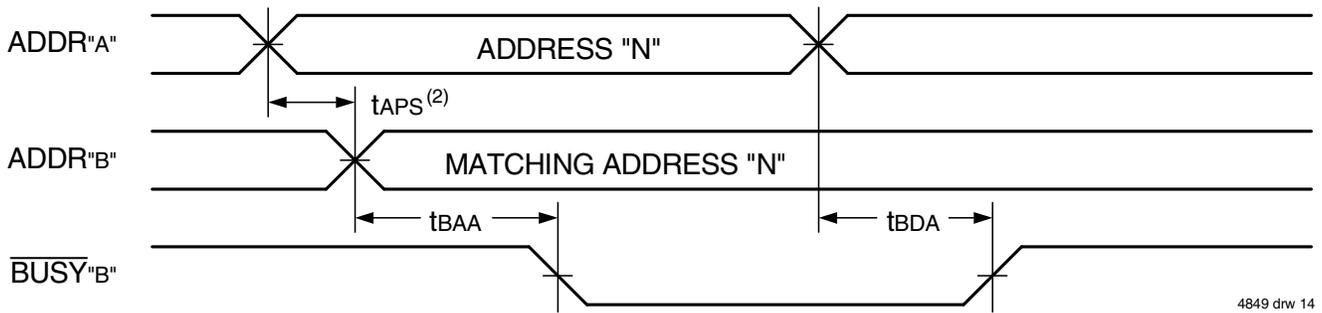
NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and \overline{BUSY} ($M/\overline{S} = V_{IH}$)".
2. To ensure that the earlier of the two ports wins.
3. t_{BDD} is a calculated parameter and is the greater of 0, t_{WDD} - t_{WP} (actual), or t_{DDD} - t_{DW} (actual).
4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".
5. To ensure that a write cycle is completed on port "B" after contention on port "A".

Waveform of **BUSY** Arbitration Controlled by **CE** Timing ($M/\bar{S} = V_{IH}$)^(1,3)



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing ($M/\bar{S} = V_{IH}$)⁽¹⁾



NOTES:

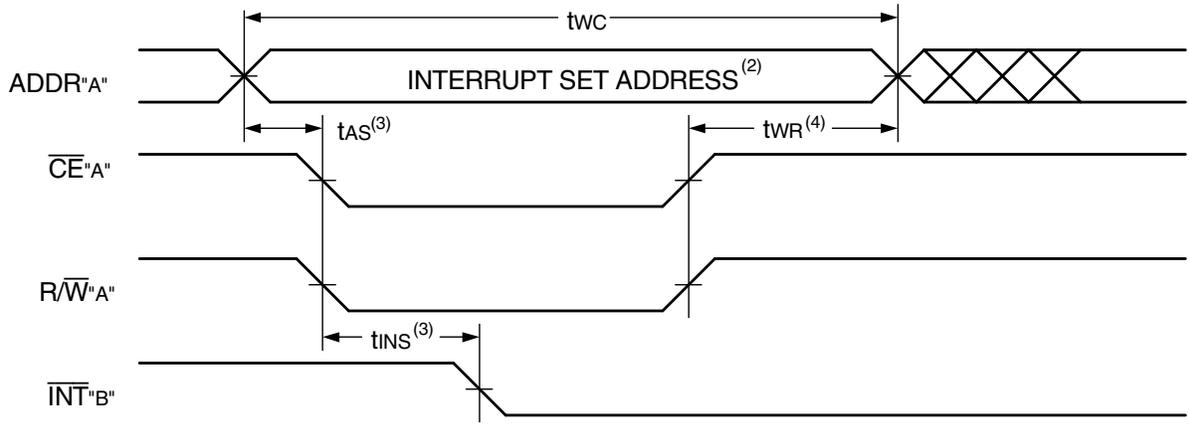
1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
2. If tAPS is not satisfied, the **BUSY** signal will be asserted on one side or another but there is no guarantee on which side **BUSY** will be asserted.
3. Refer to Truth Table I - Chip Enable.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

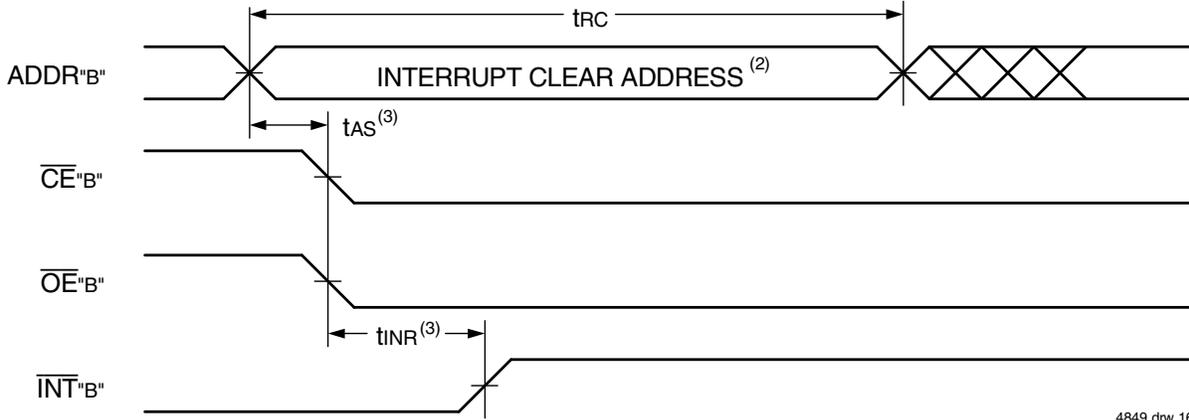
Symbol	Parameter	70V28L15 Com'l Only		70V28L20 Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
INTERRUPT TIMING						
tAS	Address Set-up Time	0	—	0	—	ns
tWR	Write Recovery Time	0	—	0	—	ns
tINS	Interrupt Set Time	—	15	—	20	ns
tNR	Interrupt Reset Time	—	15	—	20	ns

4849 tbl 15

Waveform of Interrupt Timing^(1,5)



4849 drw 15



4849 drw 16

NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
2. Refer to Interrupt Truth Table.
3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
4. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is de-asserted first.
5. Refer to Truth Table I - Chip Enable.

Truth Table IV — Interrupt Flag^(1,4,5)

Left Port					Right Port					Function
R/W _L	CE _L	OE _L	A _{15L-A_{0L}}	INT _L	R/W _R	CE _R	OE _R	A _{15R-A_{0R}}	INT _R	
L	L	X	FFFF	X	X	X	X	X	L ⁽²⁾	Set Right INT _R Flag
X	X	X	X	X	X	L	L	FFFF	H ⁽³⁾	Reset Right INT _R Flag
X	X	X	X	L ⁽³⁾	L	L	X	FFFE	X	Set Left INT _L Flag
X	L	L	FFFE	H ⁽²⁾	X	X	X	X	X	Reset Left INT _L Flag

4849 tbl 16

NOTES:

1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$.
2. If $\overline{BUSY}_L = V_{IL}$, then no change.
3. If $\overline{BUSY}_R = V_{IL}$, then no change.
4. INT_L and INT_R must be initialized at power-up.
5. Refer to Truth Table I - Chip Enable.

Truth Table V —
Address **BUSY** Arbitration⁽⁴⁾

Inputs			Outputs		Function
\overline{CE}_L	\overline{CE}_R	A _{0L} -A _{15L} A _{0R} -A _{15R}	$\overline{BUSY}_L^{(1)}$	$\overline{BUSY}_R^{(1)}$	
X	X	NO MATCH	H	H	Normal
H	X	MATCH	H	H	Normal
X	H	MATCH	H	H	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

4849 tbl 17

1. Pins \overline{BUSY}_L and \overline{BUSY}_R are both outputs when the part is configured as a master. Both are inputs when configured as a slave. \overline{BUSY} outputs on the IDT70V28 are push-pull, not open drain outputs. On slaves the \overline{BUSY} input internally inhibits writes.
2. "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If t_{APS} is not met, either \overline{BUSY}_L or \overline{BUSY}_R = LOW will result. \overline{BUSY}_L and \overline{BUSY}_R outputs can not be LOW simultaneously.
3. Writes to the left port are internally ignored when \overline{BUSY}_L outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when \overline{BUSY}_R outputs are driving LOW regardless of actual logic level on the pin.
4. Refer to Truth Table I - Chip Enable.

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	D ₀ - D ₁₅ Left	D ₀ - D ₁₅ Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

4849 tbl 18

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V28.
2. There are eight semaphore flags written to via I/O₀ and read from all I/O's (I/O₀-I/O₁₅). These eight semaphores are addressed by A₀ - A₂.
3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to Truth Table III - Semaphore Read/Write Control.

Functional Description

The IDT70V28 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V28 has an automatic power down feature controlled by \overline{CE} . The \overline{CE}_0 and \overline{CE}_1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = \text{HIGH}$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INT}_L) is asserted when the right port writes to memory location

FFFE (HEX), where a write is defined as $\overline{CE}_R = R/\overline{WR} = V_{IL}$ per Truth Table IV. The left port clears the interrupt through access of address location FFFE when $\overline{CE}_L = \overline{OE}_L = V_{IL}$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INT}_R) is asserted when the left port writes to memory location FFFF (HEX) and to clear the interrupt flag (\overline{INT}_R), the right port must read the memory location FFFF. The message (16 bits) at FFFE or FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations FFFE and FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table IV for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of $\overline{\text{BUSY}}$ logic is not required or desirable for all applications. In some cases it may be useful to logically OR the $\overline{\text{BUSY}}$ outputs together and use any $\overline{\text{BUSY}}$ indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of $\overline{\text{BUSY}}$ logic is not desirable, the $\overline{\text{BUSY}}$ logic can be disabled by placing the part in slave mode with the $\overline{\text{M/S}}$ pin. Once in slave mode the $\overline{\text{BUSY}}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{\text{BUSY}}$ pins HIGH. If desired, unintended write operations can be prevented to a port by tying the $\overline{\text{BUSY}}$ pin for that port LOW.

The $\overline{\text{BUSY}}$ outputs on the IDT70V28 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the $\overline{\text{BUSY}}$ indication for the resulting array requires the use of an external AND gate.

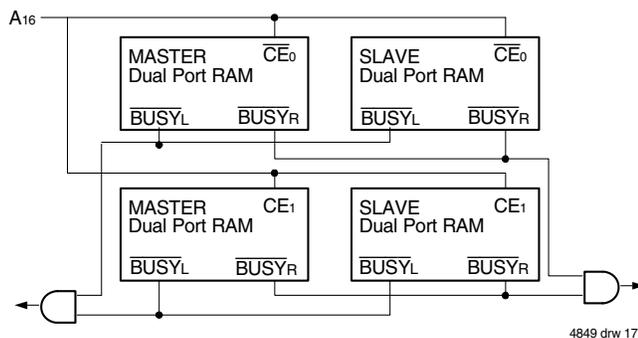


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V28 RAMs.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V28 RAM array in width while using $\overline{\text{BUSY}}$ logic, one master part is used to decide which side of the RAMs array will receive a $\overline{\text{BUSY}}$ indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the $\overline{\text{BUSY}}$ signal as a write inhibit signal. Thus on the IDT70V28 RAM the $\overline{\text{BUSY}}$ pin is an output if the part is used as a master ($\overline{\text{M/S}}$ pin = VIH), and the $\overline{\text{BUSY}}$ pin is an input if the part used as a slave ($\overline{\text{M/S}}$ pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating $\overline{\text{BUSY}}$ on one side of the array and another master indicating $\overline{\text{BUSY}}$ on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The $\overline{\text{BUSY}}$ arbitration on a master is based on the chip enable and

address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a $\overline{\text{BUSY}}$ flag to be output from the master before the actual write pulse can be initiated with the $\overline{\text{R/W}}$ signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V28 is an extremely fast Dual-Port 64K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, with both ports being completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from or written to at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by $\overline{\text{CE}}$, the Dual-Port RAM enable, and $\overline{\text{SEM}}$, the semaphore enable. The $\overline{\text{CE}}$ and $\overline{\text{SEM}}$ pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table III where $\overline{\text{CE}}$ and $\overline{\text{SEM}}$ are both HIGH.

Systems which can best use the IDT70V28 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V28s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

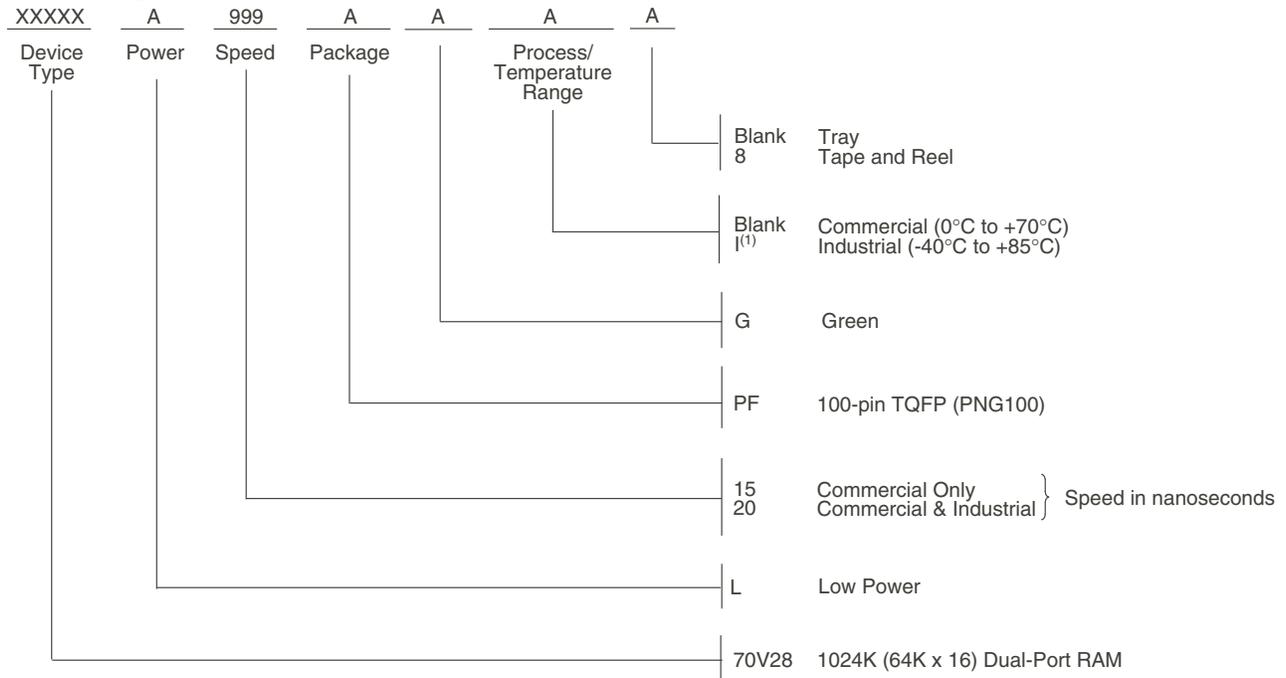
Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V28 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then

Ordering Information



4849 drw 19

NOTES:

1. Contact your sales office for Industrial Temperature range in other speeds, packages and powers.
2. **LEAD FINISH (SnPb) are Obsolete - Product Discontinuation Notice - PDN#SP-17-02**
Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
15	70V28L15PFG	PNG100	TQFP	C
	70V28L15PFG8	PNG100	TQFP	C
20	70V28L20PFG	PNG100	TQFP	C
	70V28L20PFG8	PNG100	TQFP	C
	70V28L20PFGI	PNG100	TQFP	I
	70V28L20PFGI8	PNG100	TQFP	I

Datasheet Document History

08/01/99:		Initial Public Offering
01/10/01:	Page 3	Increased storage temperature parameter
		Clarified TA Parameter
	Page 5	DC Electrical parameters—changed wording from "open" to "disabled"
		Added Truth Table I - Chip Enable as note 5
	Page 7	Corrected $\pm 200\text{mV}$ to 0mV in notes
	Page 5, 7, 10 & 12	Added Industrial Temperature information
	Page 14	Added IV to Truth Table info in "Interrupts" paragraph
	Page 17	Removed Preliminary status
01/02/02:	Page 1 & 17	Replaced IDT logo
	Pages 5, 7, 10 & 12	Removed Industrial Temperature range for 15ns from DC & AC Electrical Characteristics
01/20/06:	Page 1	Added green availability to features
	Page 17	Added green indicator to ordering information
10/23/08:	Page 17	Removed "IDT" from orderable part number
04/08/15:	Page 2	Removed IDT in reference to fabrication
	Page 2 & 17	The package code PN100-1 changed to PN100 to match standard package codes
	Page 17	Added Tape and Reel to Ordering Information
	Pages 4-6, 8 & 12-14	Corrected the text formatting for footnote that reads "Refer to Truth Table I - Chip Enable."
12/14/17:		Product Discontinuation Notice - PDN# SP-17-02
		Last time buy expires June 15, 2018
06/26/19:	Page 2	Rotated PNG100 TQFP pin configuration to accurately reflect pin 1 orientation
	Page 17	Added Orderable Part Information table



CORPORATE HEADQUARTERS
6024 Silver Creek Valley Road
San Jose, CA 95138

for SALES:
800-345-7015 or 408-284-8200
fax: 408-284-2775
www.idt.com

for Tech Support:
408-284-2794
[DualPortHelp@idt.com](mailto: DualPortHelp@idt.com)

The IDT logo is a registered trademark of Integrated Device Technology, Inc.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[IDT \(Integrated Device Technology\):](#)

[70V28L20PF18](#) [70V28L20PFG8](#) [70V28L20PF8](#) [70V28L15PF8](#) [70V28L20PFI](#) [70V28L20PFG](#) [70V28L20PFGI](#)
[70V28L15PF](#) [70V28L15PFG8](#) [70V28L20PFGI8](#) [70V28L20PF](#) [70V28L15PFG](#)

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А